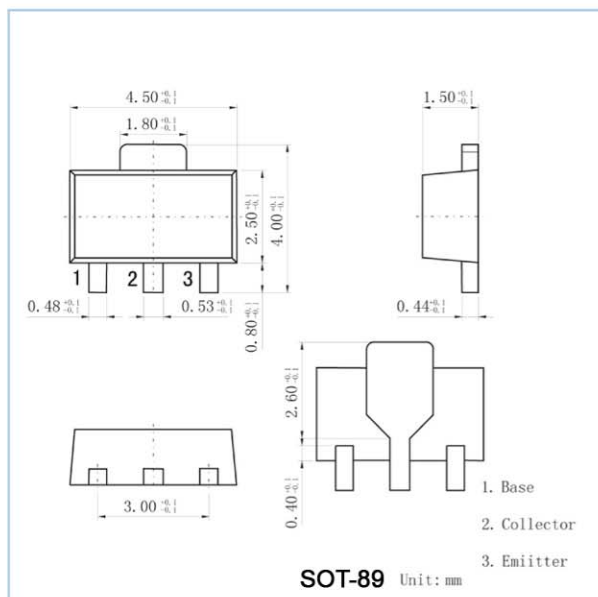


## ■ Features

- High current (max. 1 A).
- Low voltage (max. 45 V).



## ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	45	V
Collector-emitter voltage	$V_{CEO}$	45	V
Emitter-base voltage	$V_{EBO}$	5	V
Collector current (DC)	$I_C$	1	A
Peak collector current	$I_{CM}$	1.5	A
Peak base current	$I_{BM}$	0.2	A
Power dissipation $T_a \leq 25^\circ\text{C}$ *	$P_D$	1.3	W
Operating ambient temperature	$R_{amb}$	-65 to +150	$^\circ\text{C}$
Thermal resistance from junction to ambient *	$R_{th(j-a)}$	94	K/W
Thermal resistance from junction to solder point	$R_{th(j-s)}$	14	K/W
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-65 to +150	$^\circ\text{C}$

\* Device mounted on a printed-circuit board, single sided copper, tinplated, mounting pad for collector  $6\text{ cm}^2$ .

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = 30\text{ V}, I_E = 0$			100	nA
		$V_{CB} = 30\text{ V}, I_E = 0; T_j = 125^\circ\text{C}$			10	iA
Emitter cutoff current	$I_{EBO}$	$V_{EB} = 5\text{ V}, I_C = 0$			100	nA
DC current gain	$h_{FE}$	$I_C = 5\text{ mA}; V_{CE} = 2\text{ V}$	40			
		$I_C = 150\text{ mA}; V_{CE} = 2\text{ V}$	63		250	
		$I_C = 500\text{ mA}; V_{CE} = 2\text{ V}$	25			
DC current gain	$h_{FE}$	$I_C = 150\text{ mA}; V_{CE} = 2\text{ V};$	63		160	
			100		250	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500\text{ mA}; I_B = 50\text{ mA}$			0.5	V
Base to emitter voltage	$V_{BE}$	$I_C = 500\text{ mA}; V_{CE} = 2\text{ V}$			1	V
DC current gain ratio of the complementary pairs	$\frac{h_{FE}}{h_{FE}}$	$ I_C  = 150\text{ mA};  V_{CE}  = 2\text{ V}$		1.3	1.6	
Transition frequency	$f_T$	$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$		130		MHz

■  $h_{FE}$  Classification

TYPE	BCX54	BCX54-10	BCX54-16
Marking	BA	BC	BD

单击下面可查看定价，库存，交付和生命周期等信息

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